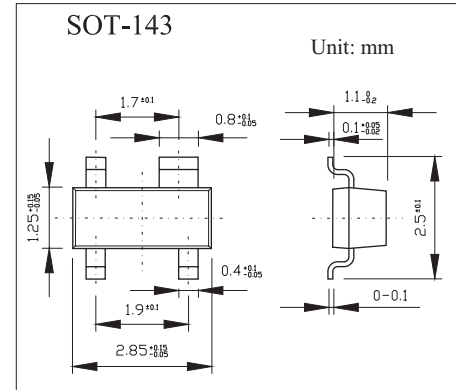


Silicon RF Switching Diode

BAR65-07

■ Features

- Low loss, low capacitance PIN-Diode
- Band switch for TV-tuners
- Series diode for mobile communications transmit-receive switch
- Unconnected pair



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	30	V
Forward current	I _F	100	mA
Operating temperature range	T _{op}	-55 to +125	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note

1. Unit Rating.Total Rating = Unit Rating × 1.5

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 20 V; T _A = 25°C			20	nA
Forward voltage	V _F	I _F = 100 mA		0.93	1	V
Diode capacitance	C _T	V _R = 1 V, f = 1 MHz		0.6	0.9	pF
		V _R = 3 V, f = 1 MHz		0.57	0.8	
Forward resistance	r _f	I _F = 5 mA, f = 100 MHz		0.65	0.95	Ω
		I _F = 10 mA, f = 100 MHz		0.56	0.9	
Series inductance	L _s			1.4		nH

■ Marking

Type	BAR65-07
Marking	M